Thyristor Diode Modules

Liujing rectifier co., Ltd.

V_{RSM}	V_{RRM} V_{DRM}	I_{TRMS} =510A(maximum value for continous operation)		
V	V	I_{TAV} =330A(sin.180; Tc=80℃)		
900	800	SKKT 330/08E	SKKH 330/08E	
1300	1200	SKKT 330/12E	SKKH 330/12E	
1700	1600	SKKT 330/16E	SKKH 330/16E	
1900	1800	SKKT 330/18E	SKKH 330/18E	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; Tc = 85(100)℃;	305(225)	A
I_D	P16/200F; Ta = 35℃; B2/B6	520/650	A
I_{RMS}	P16/200F; Ta = 35℃; W1/W3	585/3*485	A
I_{TSM}	T_{vj} = 25℃; 10ms	9500	A
	T_{vj} = 130℃; 10ms	8000	A
i^2t	T_{vj} = 25℃; 8，3 ...10ms	4510000	A^2S
	T_{vj} = 130℃; 8，3 ...10ms	320000	A^2S
V_T	T_{vj} = 25℃; I_T=990A	max.1.4	V
$V_{T(TO)}$	T_{vj} = 130℃	max.0.8	V
r_T	T_{vj} = 130℃	max.1.6	mΩ
I_{DD};I_{RD}	T_{vj} = 130℃; V_{RD}=V_{RRM} ; V_{DD}=V_{DRM}	max. 50	mA
t_{gd}	T_{vj} = 25℃; I_G = 1A; di$_G$/dt = A/μs	1	μs
t_{gr}	V_D = 0.67*V_{DRM}	2	μs
$(di/dt)_{cr}$	T_{vj} = 130℃	max.250	A/μs
$(dv/dt)_{cr}$	T_{vj} = 130℃	max.1000	V/μs
t_q	T_{vj} = 130℃	250	μs
I_H	T_{vj} = 25℃ ; typ./max	150/500	mA
I_L	T_{vj} = 25℃ ; RG = 33Ω ; typ./max	300/2000	mA
V_{GT}	T_{vj} = 25℃ ; d.c.	min. 3	V
I_{GT}	T_{vj} = 25℃ ; d.c.	min. 200	mA
V_{GD}	T_{vj} = 130℃ ; d.c.	max. 0.25	V
I_{GD}	T_{vj} = 130℃ ; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor/per module	0.11 / 0.055	K/W
$R_{th(j-c)}$	sin. 180; per thyristor/per module	0.116 / 0.058	K/W
$R_{th(j-c)}$	rec. 120; per thyristor/per module	0.13 / 0.065	K/W
$R_{th(j-c)}$	per thyristor/per module	0.04 / 0.02	K/W
T_{vj}		- 40...+ 130	℃
T_{stg}		- 40...+ 130	℃
V_{isol}	a. c. 50Hz; r.m.	3600/3000	V~
M_s	to heatsink	5 ± 15% ¹)	Nm
M_t	to terminal	9 ±15% ²)	Nm
a		5*9.81	m/s^2
m	approx.	600	g
Case	SKKH	LJ3	

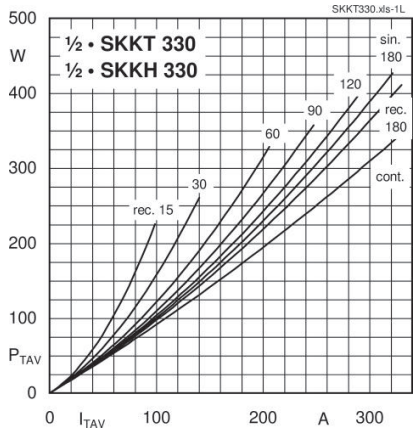


Fig. 1L Power dissipation per thyristor vs. on-state current

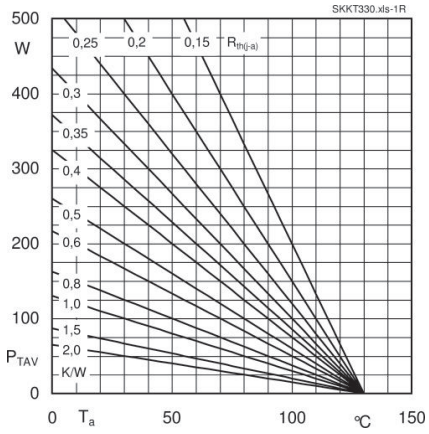


Fig. 1R Power dissipation per thyristor vs. ambient temp.

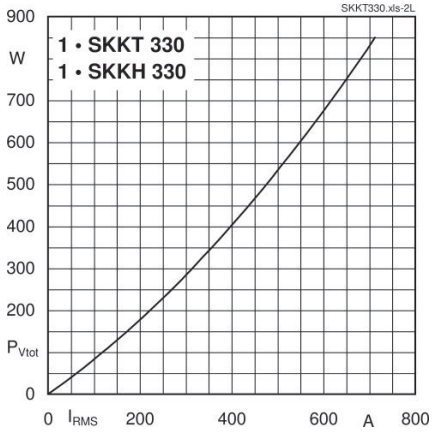


Fig. 2L Power dissipation per module vs. rms current

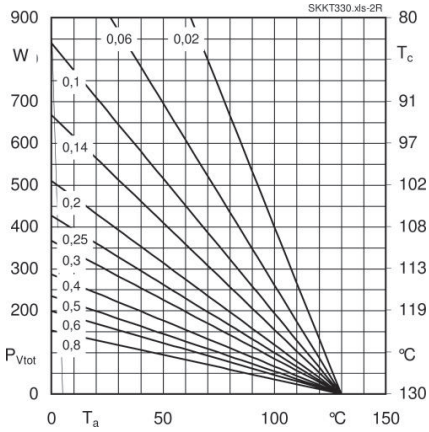


Fig. 2R Power dissipation per module vs. case temp.

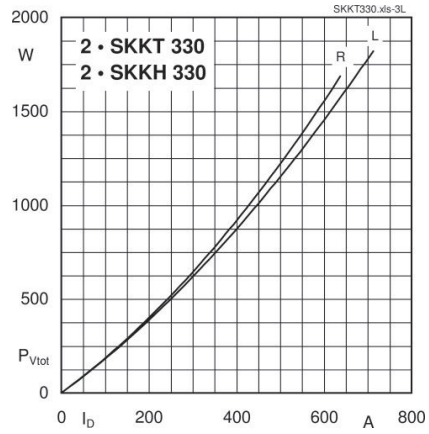


Fig. 3L Power dissipation of two modules vs. direct current

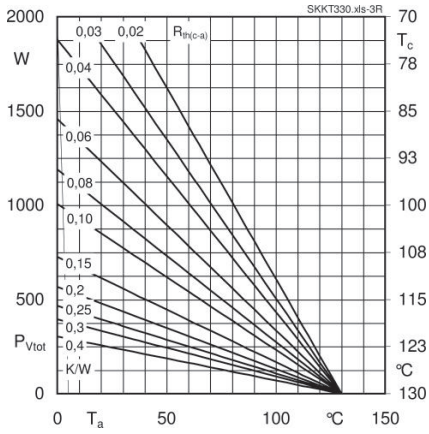


Fig. 3R Power dissipation of two modules vs. case temp.

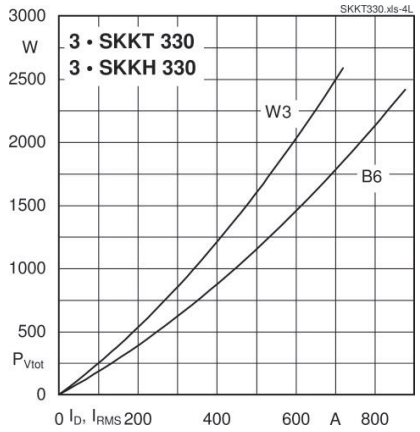


Fig. 4L Power dissipation of three modules vs. direct and rms current

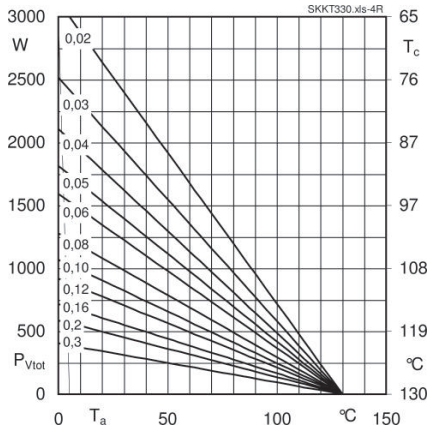


Fig. 4R Power dissipation of three modules vs. case temp.

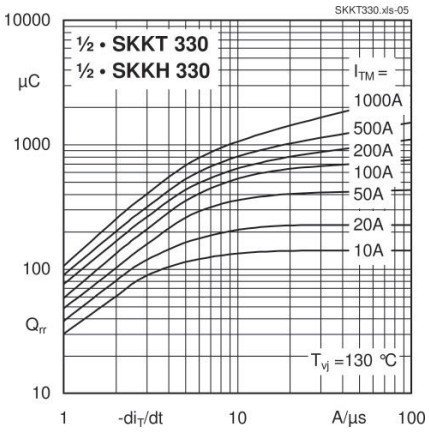


Fig. 5 Recovered charge vs. current decrease

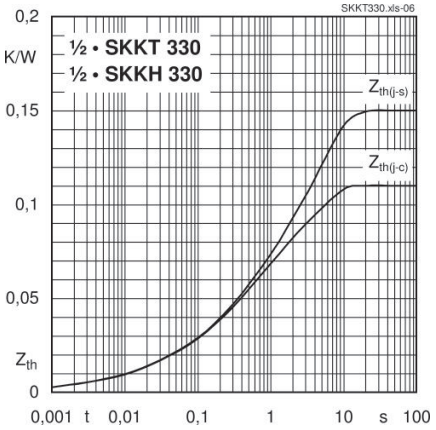


Fig. 6 Transient thermal impedance vs. time

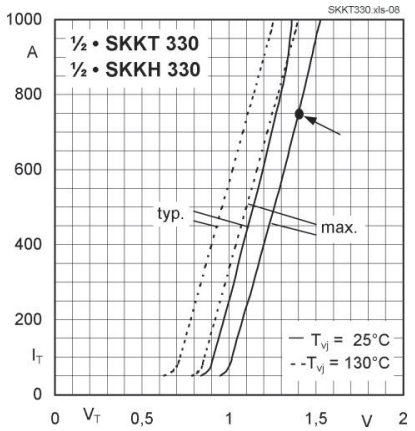


Fig. 7 On-state characteristics

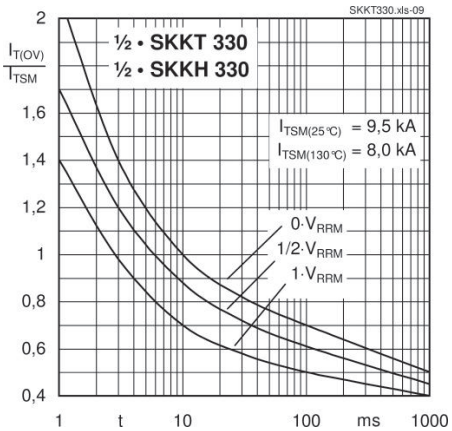
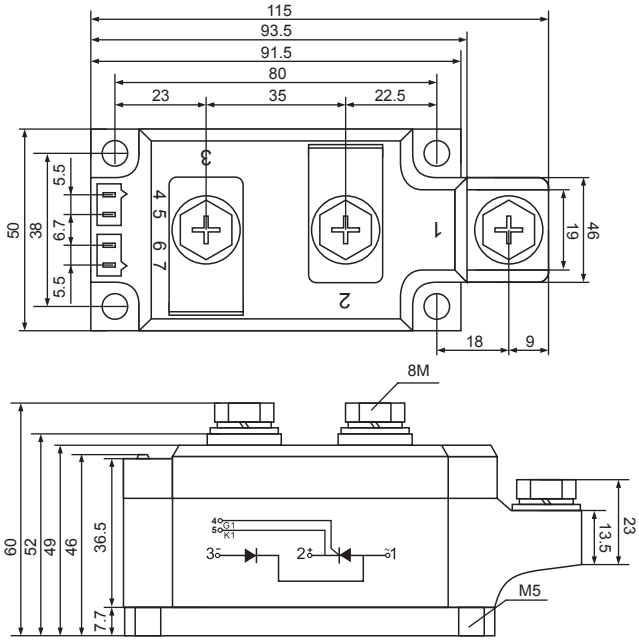


Fig. 8 Surge overload current vs. time



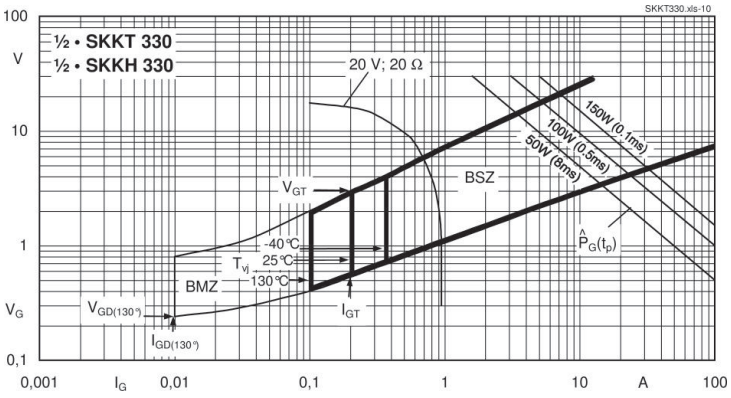


Fig. 9 Gate trigger characteristics

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